ABSTRACT OF THE DISCLOSURE

An integrated device in emitter-switching configuration is described. The device is integrated in a chip of semiconductor material of a first conductivity type which has a first surface and a second surface opposite to each other. The device comprises a first transistor having a base region, an emitter region and a collector region, a second transistor having a not drivable terminal for collecting charges which is connected with the emitter terminal of the first transistor, a quenching element of the first transistor which discharges current therefrom when the second transistor is turned off. The quenching element comprises at least one Zener diode made in polysilicon which is coupled with the base terminal of the first transistor and with the other not drivable terminal of the second transistor. The at least one polysilicon Zener diode is formed on the second surface of said chip and it comprises a polysilicon layer having at least one zone of the first conductivity type and at least one zone of a second conductivity type in order to form at least one P-N junction.